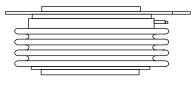


Vishay Semiconductors

Phase Control Thyristors (Hockey PUK Version), 1473 A



SHA

A-24 (K-PUK)

PRODUCT SUMMARY	
I _{T(AV)}	1473 A

FEATURES

- Center amplifying gate
- Metal case with ceramic insulator
- International standard case A-24 (K-PUK)
- High profile hockey PUK
- Compliant to RoHS Directive 2002/95/EC

TYPICAL APPLICATIONS

- DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATINGS AND CHARACTERISTICS							
PARAMETER	TEST CONDITIONS	VALUES	UNITS				
1		1473	А				
I _{T(AV)}	T _{hs}	55	°C				
L		2913	А				
I _{T(RMS)}	T _{hs}	25	°C				
1	50 Hz	20.0	А				
I _{TSM}	60 Hz	21.2	A				
l ² t	50 Hz	2000	kA ² s				
1-1	60 Hz	1865	KA-S				
l²√t		20 000	kA²√s				
V _{DRM} /V _{RRM}	Range	1200 to 2600	V				
tq	Typical	300	μs				
TJ	Range	- 40 to 125	°C				

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS								
TYPE NUMBER	VOLTAGE CODE	V _{RRM} , MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I _{RRM} MAXIMUM AT T _J = 125 °C mA				
	12	1200	1300					
	16	1600	1700					
	18	1800	1900					
ST1000CK	20	2000	2100	100				
	22	2200	2300					
	24	2400	2500					
	26	2600	2700					



ST1000C..K Series

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PARAMETER	SYMBOL		DITIONS	VALUES	UNITS	
Maximum average on-state current	1	180° condu	180° conduction, half sine wave			Α
at heatsink temperature	I _{T(AV)}	Double side	e (single side) co	oled	55 (85)	°C
Maximum RMS on-state current	I _{T(RMS)}	DC at 25 °C	heatsink temp	erature double side cooled	6540	Α
		t = 10 ms	No voltage		20.0	
Maximum peak, one-cycle,		t = 8.3 ms	reapplied		21.2	1.0
non-repetitive surge current	I _{TSM}	t = 10 ms	100 % V _{RRM}		17.0	kA
		t = 8.3 ms	reapplied	Sinusoidal half wave, initial T _J = T _J maximum	18.1	
	l ² t	t = 10 ms	No voltage reapplied 100 % V _{BBM}		2000	kA ² s
Ma 1 and 121 for for the		t = 8.3 ms			1865	
Maximum I ² t for fusing		t = 10 ms			1445	
		t = 8.3 ms	reapplied		1360	
Maximum I²√t for fusing	l²√t	t = 0.1 ms t	20 000	kA²√s		
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % x π	$x _{T(AV)} < l < \pi x$	$I_{T(AV)}$), $T_J = T_J$ maximum	0.950	v
High level value of threshold voltage	V _{T(TO)2}	$(I > \pi \times I_{T(AV)})$	$(I > \pi \times I_{T(AV)}), T_J = T_J maximum$			
Low level value of on-state slope resistance	r _{t1}	(16.7 % x π	$x I_{T(AV)} < I < \pi x$	$I_{T(AV)}$), $T_J = T_J$ maximum	0.283	
High level value of on-state slope resistance	r _{t2}	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			0.265	mΩ
Maximum on-state voltage drop	V _{TM}	I _{pk} = 3000 A	∧, T _J = 125 °C, t	_p = 10 ms sine pulse	1.80	V
Maximum holding current	Ι _Η	T 05.00			600	
Typical latching current	١L	T _J = 25 °C, anode supply 12 V resistive load				mA

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum non-repetitive rate of rise of turned-on current	dl/dt	Gate drive 20 V, 20 $\Omega,$ $t_r \leq 1~\mu s$ T_J = T_J maximum, anode voltage $\leq 80~\%~V_{DRM}$	1000	A/µs
Typical delay time	t _d	Gate current 1 A, dl _g /dt = 1 A/ μ s V _d = 0.67 % V _{DRM} , T _J = 25 °C	1.9	
Typical turn-off time	tq	I_{TM} = 550 A, T_J = T_J maximum, dI/dt = 40 A/µs, V_R = 50 V, dV/dt = 20 V/µs, gate 0 V 100 $\Omega,$ t_p = 500 µs	300	μs

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of of off-state voltage	dV/dt	$T_J = T_J$ maximum linear to 80 % rated V_{DRM}	500	V/µs
Maximum peak reverse and off-state leakage current	I _{RRM} , I _{DRM}	$T_J = T_J$ maximum, rated V_{DRM}/V_{RRM} applied	100	mA



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TRIGGERING						
PARAMETER	SYMBOL	TE	VAL	UES	UNITS	
FARAMETER	STIVIDOL		ST CONDITIONS	TYP.	MAX.	UNITS
Maximum peak gate power	P _{GM}	$T_J = T_J$ maximum,	$t_p \le 5 \text{ ms}$	1	6	w
Maximum peak average gate power	P _{G(AV)}	$T_J = T_J$ maximum,	f = 50 Hz, d% = 50	:	3	vv
Maximum peak positive gate current	I _{GM}			3	.0	А
Maximum peak positive gate voltage	$+ V_{GM}$	$T_J = T_J$ maximum,	$t_p \le 5 \text{ ms}$	20		V
Maximum peak negative gate voltage	- V _{GM}		5.0] ^v	
		T _J = - 40 °C		200	-	
DC gate current required to trigger	I _{GT}	T _J = 25 °C	Maximum required gate trigger/	100	200	mA
		T _J = 125 °C	current/voltage are the lowest	50	-	
		T _J = - 40 °C	value which will trigger all units	1.4	-	
DC gate voltage required to trigger	V _{GT}	T _J = 25 °C	12 V anode to cathode applied	1.1	3.0	V
		T _J = 125 °C		0.9	-	
DC gate current not to trigger	I _{GD}	T. T. movimum	Maximum gate current/voltage not to trigger is the maximum value which will not trigger any	n 10		mA
DC gate voltage not to trigger	V _{GD}	$T_J = T_J maximum$	0.	25	V	

THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum operating temperature range	TJ		- 40 to 125	0		
Maximum storage temperature range	T _{Stg}		- 40 to 150			
Maximum thermal resistance,	Р	DC operation single side cooled	0.042			
junction to heatsink	R _{thJ-hs}	DC operation double side cooled	0.021	к/w		
Maximum thermal resistance,	Р	DC operation single side cooled	0.006	- r∿ vv		
case to heatsink	R _{thC-hs}	DC operation double side cooled	0.003	1		
Mounting force, ± 10 %			24 500	Ν		
Mounting force, ± 10 %			(2500)	(kg)		
Approximate weight			425	g		
Case style		See dimensions - link at the end of datasheet	A-24 (K-F	PUK)		

	1					
CONDUCTION ANGLE	SINUSOIDAL	SINUSOIDAL CONDUCTION		R CONDUCTION	TEST CONDITIONS	UNITS
CONDUCTION ANGLE	SINGLE SIDE	DOUBLE SIDE	SINGLE SIDE	DOUBLE SIDE	TEST CONDITIONS	UNITS
180°	0.003	0.003	0.002	0.002		
120°	0.004	0.004	0.004	0.004		
90°	0.005	0.005	0.005	0.005	$T_J = T_J$ maximum	K/W
60°	0.007	0.007	0.007	0.007		
30°	0.012	0.012	0.012	0.012		

Note

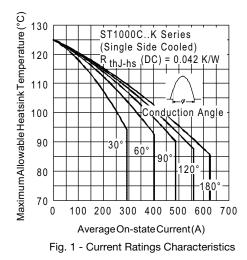
• The table above shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

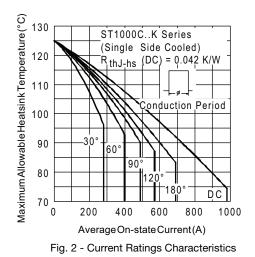
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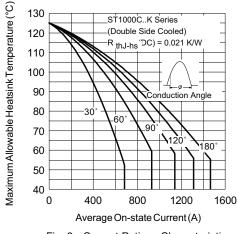
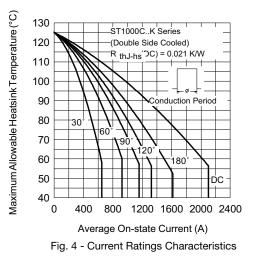


Fig. 3 - Current Ratings Characteristics



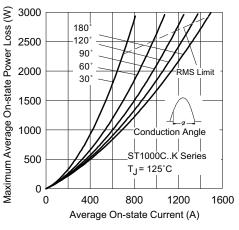
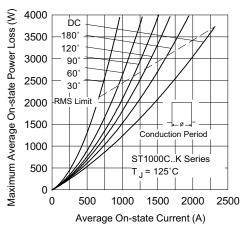
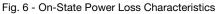


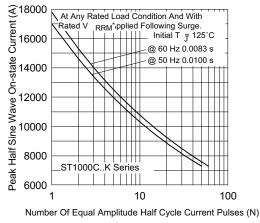
Fig. 5 - On-State Power Loss Characteristics

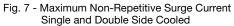


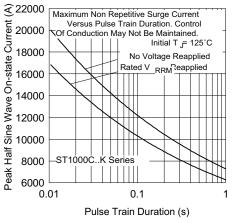


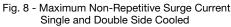


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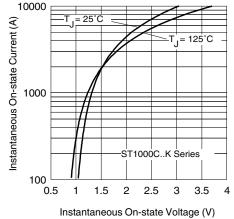
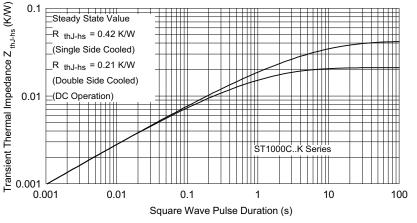


Fig. 9 - On-State Voltage Drop Characteristics





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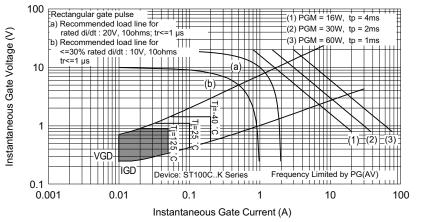


Fig. 11 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code	ST	100	0	с	26	к	1	-		
		2	3	4	5	6	7	8		
	1 2	-	ristor ential p	art numl	ber					
	3		Essential part number 0 = Converter grade							
	H		C = Ceramic PUK Voltage code x 100 = V _{RRM} (see Voltage Ratings table)							
	6		K = PUK case A-24 (K-PUK)							
	7		0 = Eyelet terminals (gate and auxiliary cathode unsoldered leads)							
			1 = Fast-on terminals (gate and auxiliary cathode unsoldered leads)							
			2 = Eyelet terminals (gate and auxiliary cathode soldered leads)3 = Fast-on terminals (gate and auxiliary cathode soldered leads)							
							-)
	8	- Crit	ical dV/	dt: ● No ● L =		0 V/µs (//µs (spe			tion)	
							<u> </u>			

LINKS TO RELATED DOCUMENTS						
Dimensions	www.vishay.com/doc?95081					

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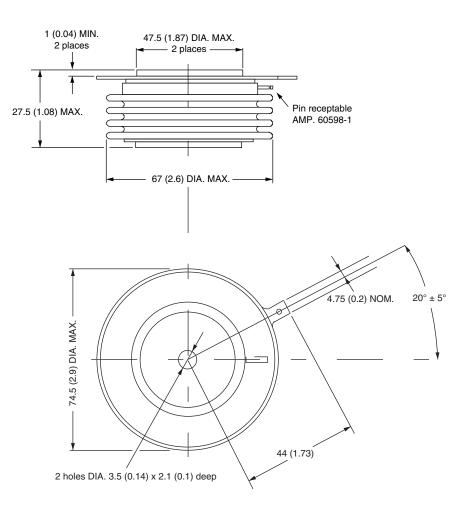


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A-24 (K-PUK)

DIMENSIONS in millimeters (inches)

Creepage distance: 28.88 (1.137) minimum Strike distance: 17.99 (0.708) minimum



Quote between upper and lower pole pieces has to be considered after application of mounting force (see thermal and mechanical specification)



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